3SK301 (Tentative), 3SK305 (Tentative)

Silicon N-Channel MOS FET

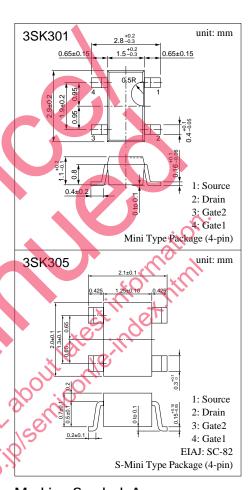
For low-voltage operating VHF amplification

■ Features

- Achieving the equivalent performance to the conventional products under low voltage operation.
- Mini-type/S-mini type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit	
Drain to Source voltage	V _{DS}	15	V	
Gate 1 to Source voltage	V _{G1S}	±8	V	
Gate 2 to Source voltage	V_{G2S}	± 8	V	
Drain current	I_{DS}	±30	mA	
Allowable power dissipation	$P_{\rm D}$	150	mW	
Channel temperature	T _{ch}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



Marking Symbol: A

VO.		المنال المنال	0.2±		E ini Type Pack	4: Gate1 IAJ: SC-82 tage (4-pin)		
■ Electrical Characteristics (T _a = 25°C) Marking Symbol: A								
Parameter	Symbol	Conditions	min	typ	max	Unit		
Drain current	I_{DS}	$V_{DS} = 3.5 V_{G1S} = 1.5 V, V_{G2S} = 3 V$	5	15	23	mA		
Gate 1 cut-off current	I _{G1SS}	$V_{DS} = V_{G2S} = 0, V_{G1S} = \pm 8V$			±20	nA		
Gate 2 cut-off current	I _{G2SS}	$V_{DS} = V_{G1S} = 0, V_{G1S} = \pm 8V$			±20	nA		
Gate 1 to Source cut-off voltage	$V_{\rm G1SC}$	$V_{DS} = 3.5V, V_{G2S} = 3V, I_{DS} = 100\mu A$	0	0.6	1.3	V		
Gate 2 to Source cut-off voltage	V _{G2SC}	$V_{DS} = 3.5V, V_{G1S} = 3V, I_{DS} = 100\mu A$	0.15	0.65	1.35	V		
Drain to Source voltage	V _{DSX}	$I_{DS} = 50\mu A, V_{G1S} = -5V, V_{G2S} = 0$	15			V		
Forward transfer admittance	Y _{fs}	$V_{DS} = 3.5V, I_{DS} = 10mA, V_{G2S} = 3V$	17	23	29	mS		
Input capacitance (Common Source)	C _{iss}	V 10V V 5V	2	2.7	3.5	pF		
Output capacitance (Common Source)	Coss	$V_{DS} = 10V, V_{G1S} = V_{G2S} = -5V$ f = 1MHz	1	1.3	1.5	pF		
Reverse transfer capacitance (Common Source)	C _{rss}	1 — 11V1171Z			0.02	pF		
Power gain	PG	$V_{DS} = 3.5V, I_{D} = 8mA, V_{G2S} = 3V$	23.5	25.5	28.5	dB		
Noise figure	NF	f = 200MHz		2.3	2.6	dB		

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